

REMARKS

Claim 10 requires a covering on the first trench and the semiconductor structure, the cover being thicker along the center line of the first trench than over the semiconductor structure. An opening defines the region for a second trench extending perpendicular to the length of the first trench.

Claim 10 was rejected under Section 102 based on Nishida. Certainly, in Nishida, there is no way to argue that there are two trenches that extend perpendicular to one another, as specifically recited, wherein the opening to define a region for a second trench extending perpendicular to a length of the first trench. It is believed that it was argued that by going through the bottom of the first trench this is somehow perpendicular to the first trench. But, clearly, it is parallel to the length of the first trench because the trench 103c in Figure 6 of Nishida extends along the length of the trench 103b. To further clarify the point, it is asserted that the opening extends both perpendicular to the length of the first trench and across the length of the first trench. Therefore, the rejection based on Nishida should be reconsidered.

Likewise, the patent to Wen, which was not applied to claim 10, does teach the combination of the perpendicular first trench and second opening, together with the cover being thicker along a center line of said first trench than over the semiconductor structure.

With respect to claim 21, it has been amended to include the subject matter of dependent claim 25 with some additional amendments.


Claim 25 was rejected based on Wen and, particularly, its Figure 5. However, at the instance of time indicated in Figure 5, Wen does not meet the limitation of claim 21, upon which claim 25 depended, that the covering in the first trench and over the semiconductor structure be such that the covering has an opening therethrough, the opening in communication with the second trench. In other words, there is no instance of time, in any stage of Wen, that meets both requirements of original claim 21 and dependent claim 25. The subject matter formerly in dependent claim 25 has also been clarified to require that the covering that is over the semiconductor structure be thinner than a portion of the covering along the center line of the first trench.

Moreover, claim 21 has been amended to call for a covering in the first trench to be thicker away from the center line than along the center line. This is shown, for example, in Figures 2 and 3 of the present application.

In view of these remarks, reconsideration is requested.

Respectfully submitted,

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